

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph beginning on page 4, line 24, as follows:

According to the present invention, the treatment of the sapphire substrate with nitric acid solution after the H₂ cleaning is carried out under the conditions at a nitric acid (HNO₃) concentration of ~~6% to 63%~~ 6-63 wt. % and a temperature of 40°C for 0 to 10 minutes (min). In contrast, the conventional high-temperature nitriding (comparative example) is carried out under the conditions at a temperature of 750°C to 1100°C and a partial pressure of NH₃ of 50% for 5 minutes (min).